

H8550Q

S-H8550Q

General Purpose Transistors PNP Silicon

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- High current capacity in compact package.
IC =-1.5A.
- Epitaxial planar type.
- Pb-Free Package is available.

2. DEVICE MARKING AND ORDERING INFORMATION

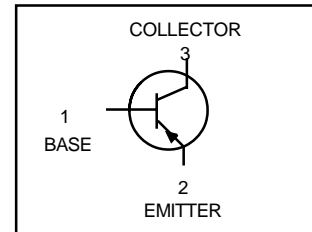
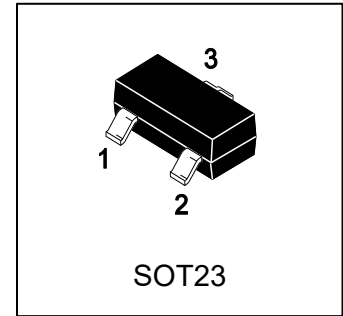
Device	Marking	Shipping
H8550Q	KIY	3000/Tape&Reel

3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-Emitter Voltage	VCEO	-50	V
Collector-Base voltage	VCBO	-50	V
Emitter-Base Voltage	VEBO	-6	V
Collector current	IC	-1500	mA

4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Power Dissipation	PD	225	mW
Junction and Storage temperature	TJ,Tstg	-55~+150	°C

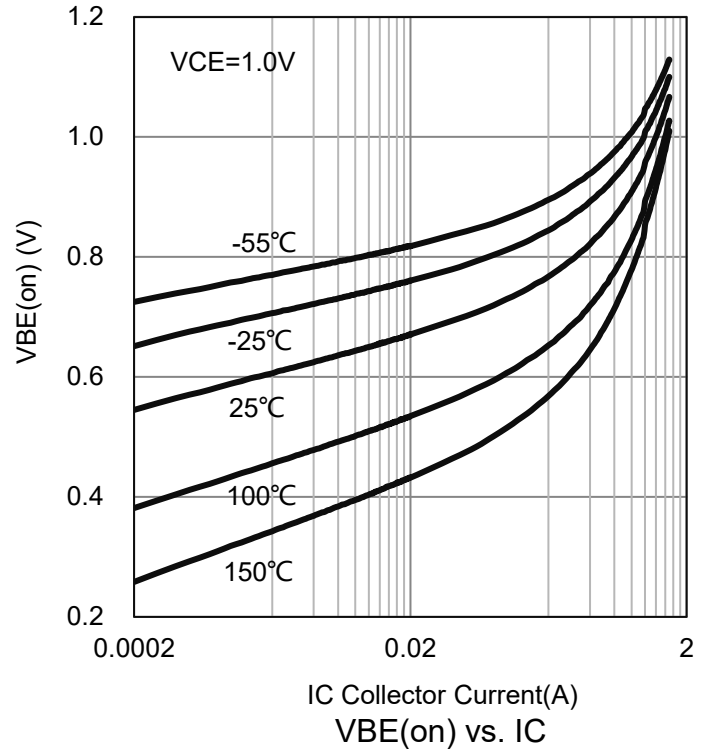
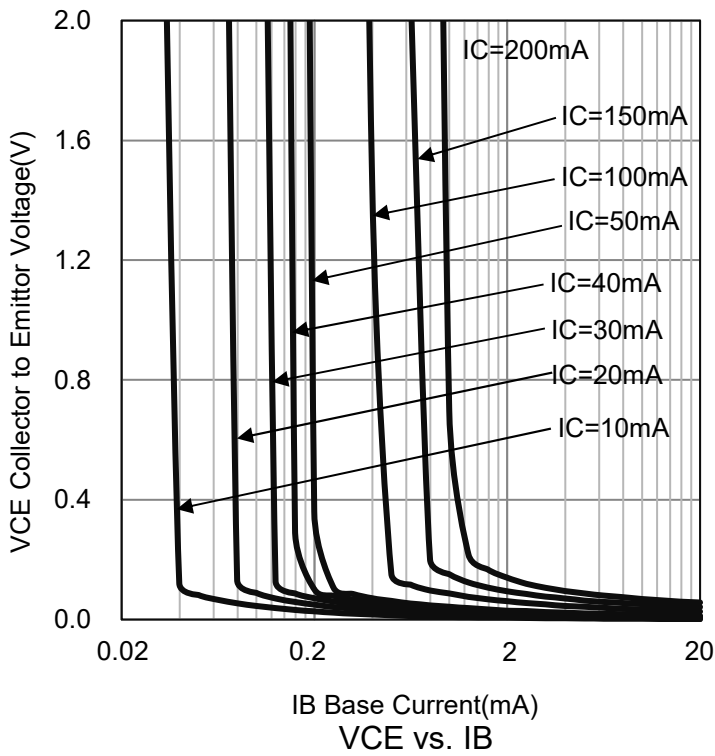
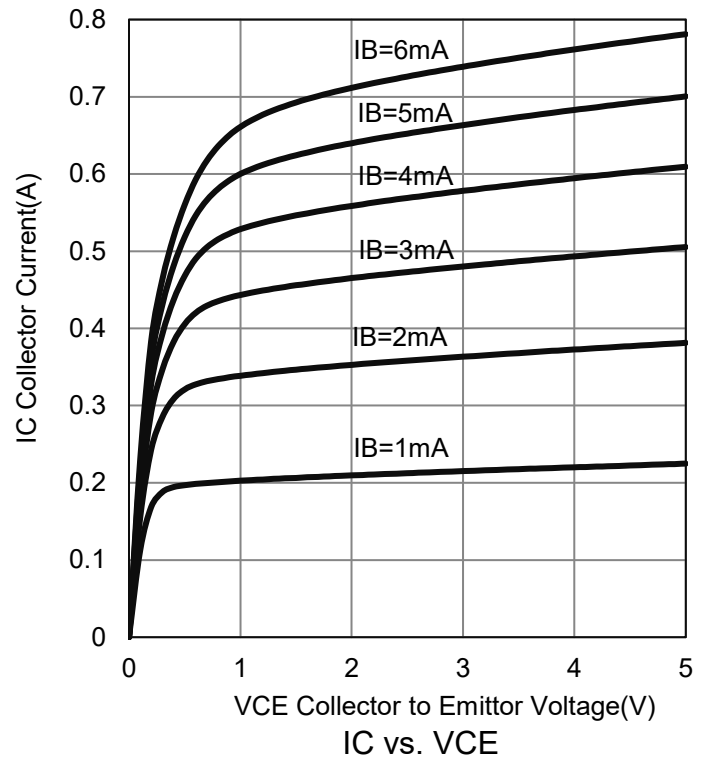
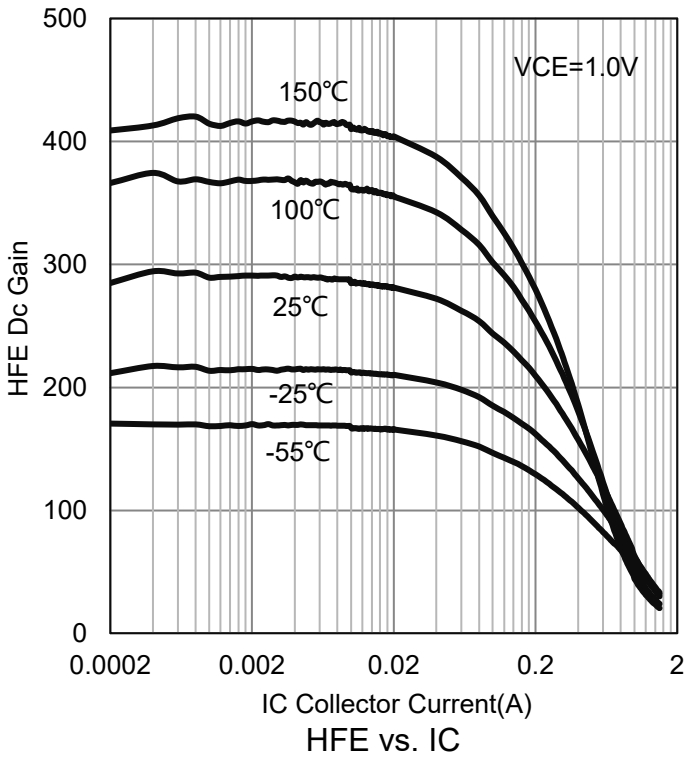


5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

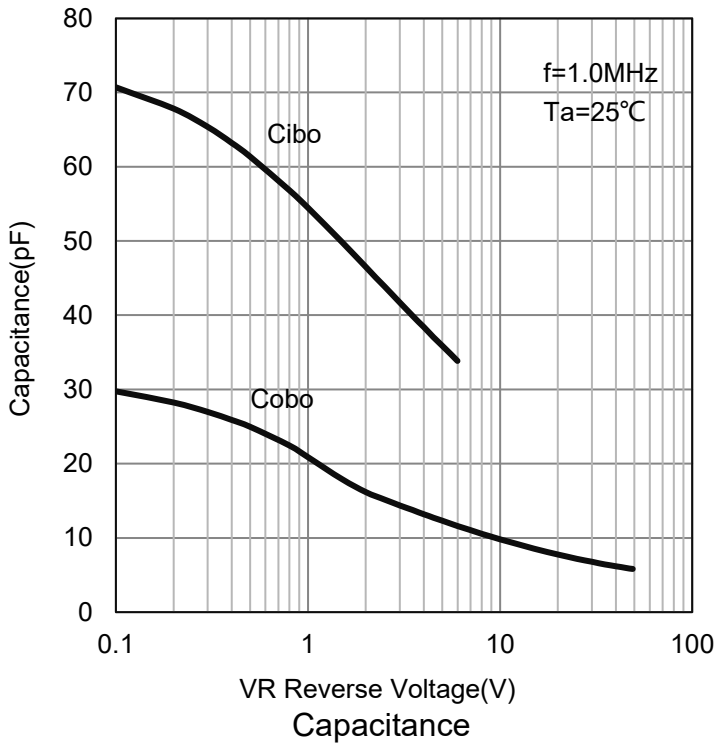
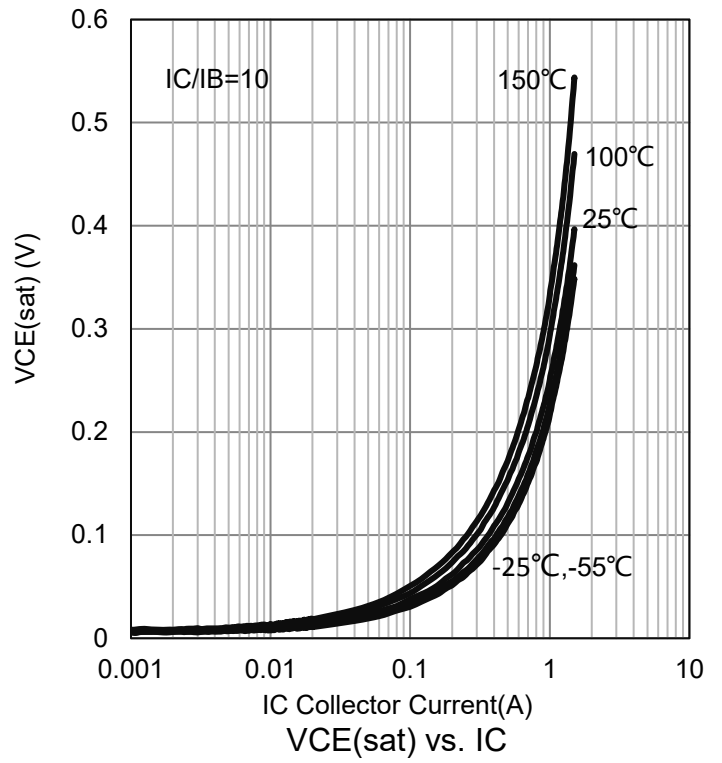
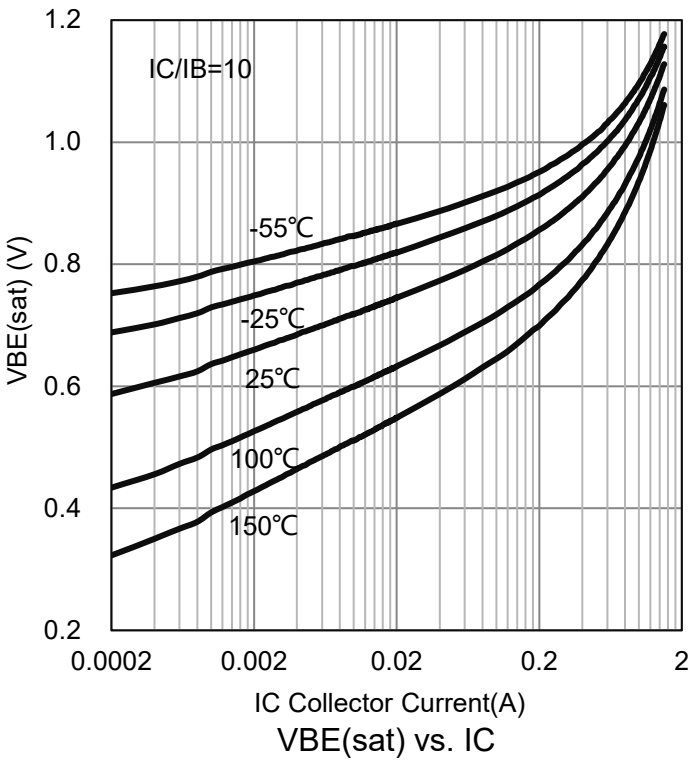
Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector-Emitter Breakdown Voltage (IC =-2.0mA,IB =0)	V(BR)CEO	-50	-	-	V
Emitter-Base Breakdown Voltage (IE = -100μA,IC=0)	V(BR)EBO	-6	-	-	V
Collector-Base Breakdown voltage (IC = -100μA,IE=0)	V(BR)CBO	-50	-	-	V
Collector Cutoff Current (VCB = -35 V,IE=0)	ICBO	-	-	-100	nA
Emitter Cutoff Current (VEB = -6V,IC=0)	IEBO	-	-	-100	nA
Base-Emitter Voltage (VCE =-1V,IC =-10mA)	VBE	-	-0.66	-1	V
DC Current Gain (IC =-100mA, VCE =-1V) (IC=-800mA, VCE =-1V)	HFE	160 40	- -	320 -	
Collector-Emitter Saturation Voltage (IC =-800mA, IB =-80mA)	VCE(S)	-	-	-0.5	V



6.ELECTRICAL CHARACTERISTICS CURVES



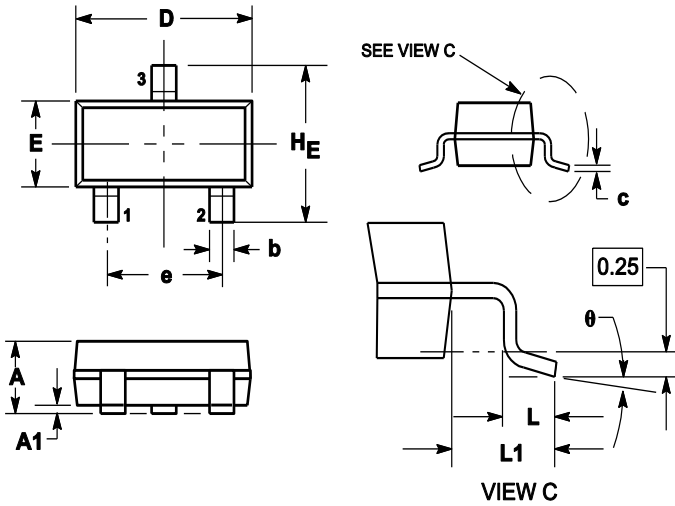
6.ELECTRICAL CHARACTERISTICS CURVES(Con.)



7. OUTLINE AND DIMENSIONS

Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1	1.11	0.035	0.04	0.044
A1	0.01	0.06	0.1	0.001	0.002	0.004
b	0.37	0.44	0.5	0.015	0.018	0.02
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.9	3.04	0.11	0.114	0.12
E	1.20	1.3	1.4	0.047	0.051	0.055
e	1.78	1.9	2.04	0.07	0.075	0.081
L	0.10	0.2	0.3	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.4	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

8. SOLDERING FOOTPRINT

